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# ***Oxide-based Materials and Devices XII***

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# Contents

---

## GALLIUM OXIDE MATERIALS AND DEVICES I

---

- 11687 07 **Enhancing the dielectric constant of oxides via acceptor-donor co-doping (Invited Paper)**  
[11687-4]
- 11687 09 **Split Ga vacancies: abundant defects in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> (Invited Paper)** [11687-6]
- 11687 0E **Trapping processes and band discontinuities in Ga<sub>2</sub>O<sub>3</sub> FinFETs investigated by dynamic characterization and optically-assisted measurements** [11687-10]

---

## GALLIUM OXIDE MATERIALS AND DEVICES II

---

- 11687 0Q **Progress in atomic layer deposited  $\alpha$ -Ga<sub>2</sub>O<sub>3</sub> materials and solar-blind detectors (Invited Paper)** [11687-20]
- 11687 0T **Detailed investigation of MOCVD grown  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> through quantitative defect spectroscopies (Invited Paper)** [11687-23]

---

## FIRST-PRINCIPLE CALCULATIONS OF MATERIAL AND DEVICE PROPERTIES

---

- 11687 0X **First-principles calculations of N- and P-type doping in wurtzite and zincblende GaN (Invited Paper)** [11687-27]

---

## PLASMONICS

---

- 11687 12 **La-doped BaSnO<sub>3</sub> films for near- and mid-infrared plasmonic applications** [11687-32]
- 11687 13 **The role of oxide defect chemistry in the drude and plasmonic response of optical fiber-based sensing layers for high-temperature gas sensing** [11687-33]

---

## ZINC OXIDE MATERIALS AND DEVICES

---

- 11687 1E **Investigation of the optical, electrical, and elemental properties upon annealing of spatial atomic layer deposited (SALD) Al-doped ZnO thin films** [11687-44]

---

#### OXIDE THIN-FILM TRANSISTORS

---

- 11687 1F **Bendable metal oxide thin-film transistors and circuits for analog electronics applications (Invited Paper)** [11687-46]
- 11687 1G **Oxide transistors: unconventional architectures and their applications (Invited Paper)** [11687-47]
- 11687 1I **Aluminum oxide as a dielectric and passivation layer for (flexible) metal-oxide and 2D semiconductor devices (Invited Paper)** [11687-49]

---

#### OXIDE-BASED EMERGING PROCESSES AND APPLICATIONS I

---

- 11687 1L **Oxides based resistive switching memories (Invited Paper)** [11687-52]
- 11687 1U **Effect of annealing on properties and performance of HfO<sub>2</sub>/SiO<sub>2</sub> optical coatings for UV-applications** [11687-60]

---

#### OXIDE-BASED EMERGING PROCESSES AND APPLICATIONS II

---

- 11687 1X **Synthesis of low dimensional oxide based complex materials by a vapor-solid method (Invited Paper)** [11687-62]
- 11687 1Y **A walk on the frontier of energy electronics with power ultra-wide bandgap oxides and ultra-thin neuromorphic 2D materials (Invited Paper)** [11687-63]
- 11687 1Z **Chemical beam vapor deposition technique with Sybilla equipment: review of main results in its 20-year anniversary (Invited Paper)** [11687-64]

---

#### POSTER SESSION

---

- 11687 25 **Parity-Time symmetry in lasers with nonuniform and segmented gain** [11687-69]
- 11687 27 **Lanthanide-doped down-conversion fluorides: synthesis, characterization, and applications** [11687-71]
- 11687 2A **Mg-related charge transitions in Mg-doped Ga<sub>2</sub>O<sub>3</sub>** [11687-74]
- 11687 2D **Sharp/tuneable UVC selectivity and extreme solar blindness in nominally undoped Ga<sub>2</sub>O<sub>3</sub> MSM photodetectors grown by pulsed laser deposition** [11687-82]